



Generation of High Peak Power Pulses With Controllable Repetition Rate in Doubly Q-Switched Laser With AOM/SnSe₂

Jingxuan Xia*, Xu Dong and Hanming Yuan

School of Physics, Changchun University of Science and Technology, Changchun, China

By simultaneously employing self-made SnSe₂ saturable absorber (SA) and an acousto-optic modulator (AOM), a dual-loss-modulated Q-switched Nd:YVO₄ laser with short pulse width, high peak power and adjustable pulse repetition rate is presented. The maximum pulse peak power of 37.57 KW with the minimum pulse duration of 5.52 ns were obtained under the pump power of 8 W and the pulse repetition rate of 5 kHz. The experimental results demonstrate that the dual-loss modulation technology with AOM and SnSe₂ SA is a simple and efficient method to generate short pulses with high peak power and adjustable low repetition rates.

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*Correspondence:

Jingxuan Xia
fredxia001@163.com

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1 INTRODUCTION

Stable solid-state pulsed laser sources with large pulse energy and peak power are used in a variety of applications, ranging from basic research to industrial material processing, medicine and telecommunications [1–3]. The use of a saturable absorber (SA) to generate pulsed lasers has been the most popular approach nowadays. In recent years, stimulated by the successful application of graphene, many two-dimension (2D) materials with layered structure have been rediscovered as promising and interesting SA materials due to their advantages of ultra-fast recovery time, broadband saturable absorption and simple fabrication process [4–7]. Tin diselenide (SnSe₂), an environmentally friendly and earth-abundant material, as a member of the 2D materials family, has gained wide attention in communications, microelectronics, lasers and nonlinear optical fields due to its unique properties, low toxicity and low cost [8, 9]. Because of the adjustable band gap characteristics, SnSe₂ has obvious broadband saturable absorption characteristics. The indirect band-gap of few layers and large bulk SnSe₂ ranges from 1.07 (~1159 nm) to 1.69 eV (~734 nm), corresponding to the direct band-gap ranges from 1.84 to 2.04 eV, respectively [10]. The indirect band-gap of few layers SnSe₂ indicates the ability of the SnSe₂ saturable absorber at 1 μm. The nonlinear optical property of multilayer SnSe₂ at 1 μm was first reported by Cheng et al in 2017, a passively Q-switched waveguide solid-state laser based on SnSe₂-SA was achieved with a minimum pulse width of 129 ns and pulse energy of 6.5 nJ [10]. In 2018, Zhang et al. reported a high power passively Q-switched Yb-doped fiber laser based on SnSe₂-SA [11]. So far, the nonlinear optical response of SnSe₂ has been widely studied by Q-switched or mode-locked lasers of different wavebands [12–15]. However, researches on pulse modulation characteristic of SnSe₂ in solid-state laser is not enough.

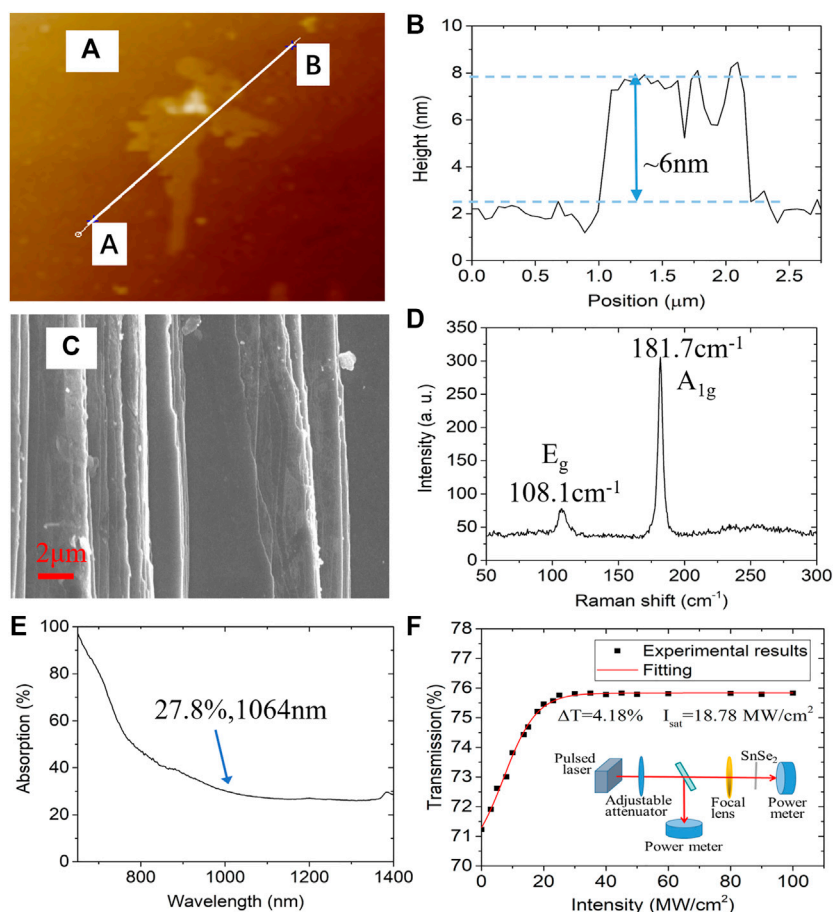


FIGURE 1 | (A) AFM image; **(B)** the corresponding heights of the AFM image; **(C)** SEM image; **(D)** Raman spectrum; **(E)** Absorption spectrum of the SnSe₂ film; **(F)** Nonlinear transmittance curve of the SnSe₂-SA.

As we know, using the dual-loss modulation mechanism, the poor stability and the difficult controllability of pulse characteristics in singly passively Q-switched lasers can be significantly improved [16–19]. Especially in the active-passively doubly Q-switched laser, the pulse duration can be compressed greatly to shorter than that of single passive modulated laser, while the pulse repetition rate can be controlled by the active modulator. Thus, pulses with high peak power, controllable repetition rate and excellent stability could be expected. However, there is no report on SnSe₂ for all-solid-state dual-loss modulation Q-switched lasers at 1.06 μm.

In this work, with our self-made SnSe₂-SA and an acousto-optic modulator (AOM), a diode-pumped doubly Q-switched laser was presented. With the maximum pump power of 8 W and AOM repetition rate of 5 kHz, the maximum pulse peak power of 37.57 KW with minimum pulse duration of 5.52 ns were obtained. For comparison, the output performances of single passive Q-switched laser with SnSe₂-SA and single active Q-switched laser with AOM in our experiment were also investigated.

2 PREPARATION AND CHARACTERIZATION OF FEW-LAYERED SNSE₂-SA

The SnSe₂ nanosheet we used as SA was fabricated by the liquid-phase exfoliation method. 30 mg SnSe₂ powder and 10 ml absolute ethylalcohol were mixed in a centrifuge tube. After 12 h sonication process, the SnSe₂ dispersions used in our experiment can be obtained. In order to fabricate evenly distributed SnSe₂ film, the spin coating method was used to prepare SnSe₂ SA. 10 μl dispersions was absorbed by suction pipet and dripped onto a quartz plate with a size of 30 mm × 30 mm × 0.5 mm. The quartz substrate was placed in the center of a spinner with a speed of 300 rpm. Soon, the SnSe₂ dispersions on the substrate was dried and a high quality SnSe₂-SA was well prepared.

The flake thicknesses of SnSe₂ were measured via atomic force microscopy (AFM), which is shown in **Figure 1A**. The corresponding height profile, presented in **Figure 1B**, shows the average thickness of ~6 nm, corresponding to about ~10 layers [10].

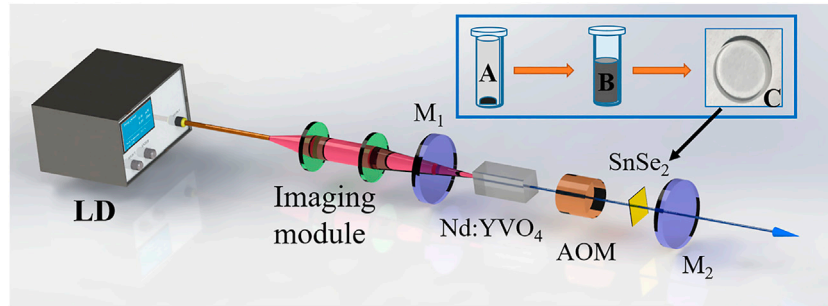


FIGURE 2 | Schematic of the doubly Q-switched laser with AOM and SnSe₂-SA.

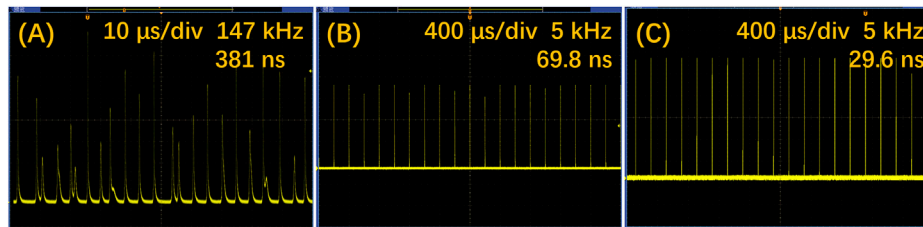


FIGURE 3 | Oscilloscope traces of the Q-switched pulse trains at the pump power of 2W: (A) single SnSe₂ SA Q-switching; (B) single AOM Q-switching; (C) double Q-switching.

The AFM is still not intuitive to observe the layered structure of the SnSe₂ SA. Therefore, the microstructures of SnSe₂ were recorded by a scanning electron microscope (SEM) with an optical resolution of 2 μm, shown in **Figure 1C**. From the figure, it can be found that well-layered structure of the SnSe₂ nanosheets were prepared in our work. The Raman spectrum was

recorded and shown in **Figure 1D**, which demonstrated the atomic structural arrangement of the fabricated film. From the figure, the E_g mode and the A_{1g} mode can be observed and located at 108.1 cm⁻¹ and 181.7 cm⁻¹, respectively. The linear absorption of SnSe₂ was measured by a Hitachi U-4100 spectrophotometer and shown in **Figure 1E**. One can see the SnSe₂ film possesses broadband absorption characteristics and the measured absorption of the SnSe₂ film was 27.8% at 1,064 nm. In order to confirm the saturable absorption capability of the SnSe₂-SA sample near 1 μm, the nonlinear transmission was measured and given in **Figure 1F**. By fitting the experimental data, the modulation depth and saturation intensity were determined to be 4.18% and 18.78 MW/cm², respectively.

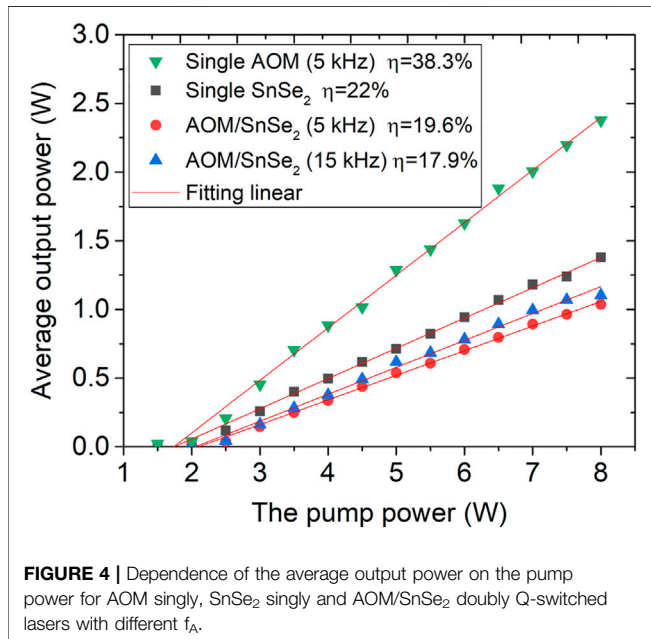
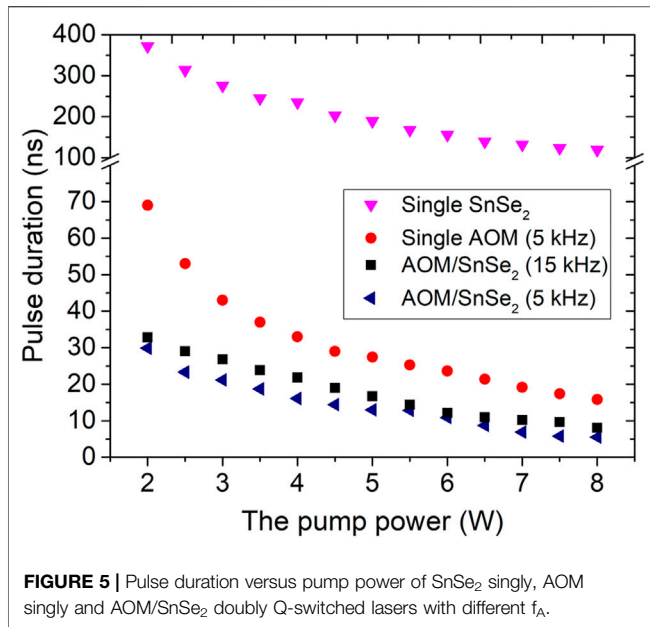


FIGURE 4 | Dependence of the average output power on the pump power for AOM singly, SnSe₂ singly and AOM/SnSe₂ doubly Q-switched lasers with different f_a .

3 EXPERIMENTAL SETUP AND RESULTS

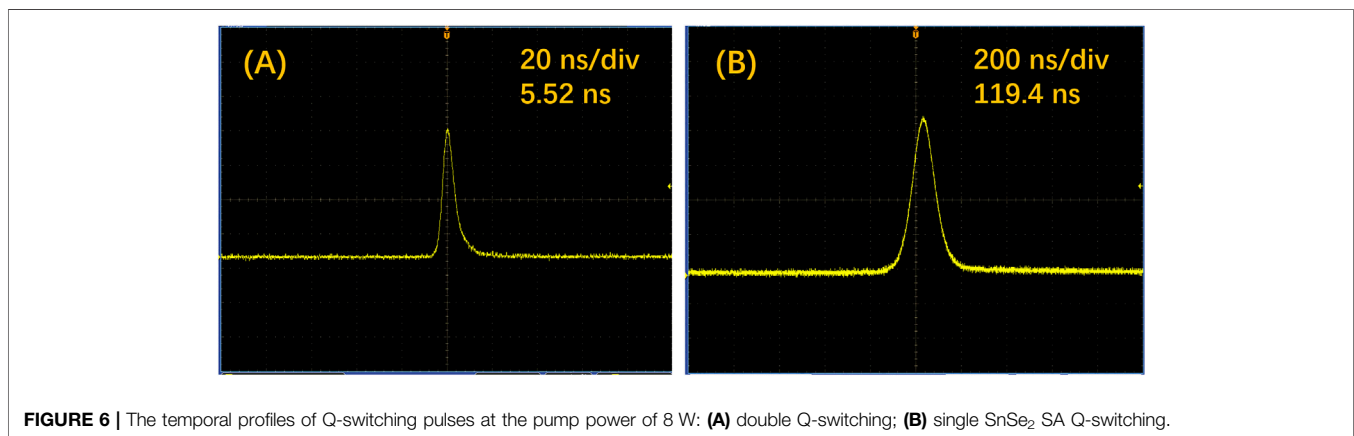
3.1 Experimental Setup

The schematic of the doubly Q-switched laser with AOM and SnSe₂-SA was demonstrated in **Figure 2**. Mirrors M₁ and M₂, acting as the resonator mirrors, are both plane mirrors. M₁, as the input mirror, is high antireflection (AR) coated at 808 nm and high-reflection (HR) coated at 1,064 nm. The transmittance of the output mirror M₂ is 15% at 1,064 nm. A 3 × 3 × 6 mm Nd:YVO₄ crystal, which is AR coated at 808 and 1,064 nm on both light-pass faces, is used as the laser medium with the Nd-doping concentration of 0.5 at. %. The laser is pumped by a commercial fiber-coupled diode laser at 808 nm with a 1:0.8 optical coupling system. An acousto-optic modulator (AOM) (GOOCH &



trains for the three kinds of lasers are shown in **Figure 3**. Obviously, the pulse stability of dual-loss-modulated laser was greatly improved.

The output performances of Nd:YVO₄ Q-switched laser with AOM/SnSe₂ and single SnSe₂ were all investigated, respectively. **Figure 4** shows the output powers versus the pump power for SnSe₂ singly, AOM singly and AOM/SnSe₂ doubly Q-switched lasers, respectively. With the increase of the pump power, the average output power increased linearly with slope efficiencies of 38.3%, 22%, 19.6% and 17.9% for SnSe₂ singly, AOM singly ($f_A = 5$ kHz) and AOM/SnSe₂ doubly Q-switched lasers at $f_A = 5$ and 15 kHz, respectively. For the singly actively Q-switched laser with AOM ($f_A = 5$ kHz) and singly passively Q-switched laser with SnSe₂, the maximum output power of 2.38 and 1.38 W were obtained at the pump power of 8 W, respectively. Because of the higher insertion loss, the output power of dual-loss-modulated laser with AOM/SnSe₂ was smaller than that of single modulated laser. At the pump power of 8 W, the maximum output power of 1.03 and 1.1 W were obtained for $f_A = 5$ and 15 kHz, respectively. A larger modulation frequency is conducive to get a higher output power.



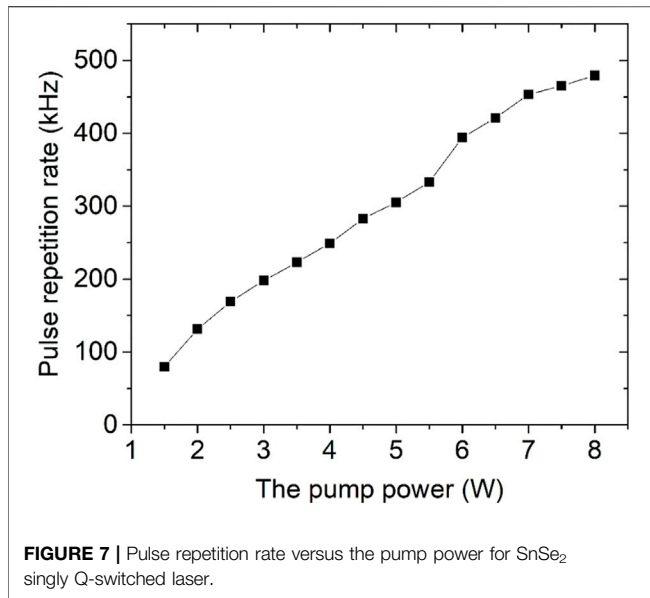
HOUSEG) is employed as the active modulator. The total cavity length is about 13.5 cm, which refers to the distance between M_1 and M_2 .

3.2 Experimental Results and Discussion

Firstly, for comparison, the output performance of Nd:YVO₄ singly actively Q-switched laser with AOM was investigated. Then, add the SnSe₂-SA into the cavity, the dual-loss-modulated Q-switched laser with AOM and SnSe₂-SA can be obtained. In this doubly Q-switched laser, the repetition rate of the Q-switched pulses mainly depends on the modulation frequency (f_A) of AOM. In order to study the influence of different modulation frequencies on pulse characteristics, the doubly Q-switched laser performances at $f_A = 5$ and 15 kHz were recorded, respectively. If the AOM is off, the laser operated in the singly passively Q-switched state, in which the Q-switched pulse repetition rates varied with the pump power. The oscilloscope traces of the Q-switched pulse

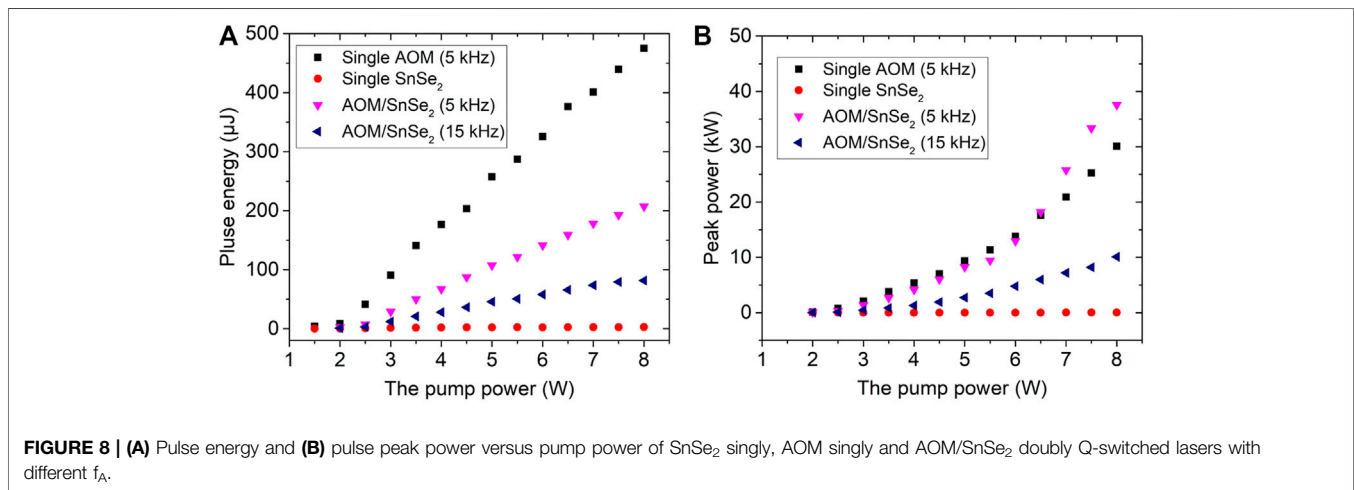
The variation of the pulse duration versus the pump power is shown in **Figure 5**. For Q-switched lasers with single AOM ($f_A = 5$ kHz) and single SnSe₂, the shortest pulse durations of 15.8 and 119.4 ns were obtained at the pump power of 8 W, respectively. Here, the pulse durations we obtained are the shortest one ever reported in passively Q-switched lasers with SnSe₂ SA [10, 14, 20–23]. To the best of our knowledge, in near-infrared region, the shortest pulse durations of 129 ns was achieved in a passively Q-switched Nd:YAG waveguide laser with SnSe₂ SA [10].

For the doubly Q-switched lasers with AOM/SnSe₂, the pulse width was much smaller than that of singly Q-switched lasers. The shortest pulse durations of 5.52 and 8.1 ns were obtained at $f_A = 5$ and 15 kHz, respectively. Obviously, a lower repetition rate can bring about a shorter pulse duration. The maximum compression ratio calculated from **Figure 5** is approximated to 95.4% from 119.4 ns (in SnSe₂ Q-switched lasers) to 5.52 ns (in



8 W, 2.8, 475.2, 207.4, and 81.7 μ J pulse energies were achieved for SnSe₂ singly, AOM singly ($f_A = 5$ kHz) and AOM/SnSe₂ doubly Q-switched lasers at $f_A = 5$ and 15 kHz, respectively, corresponding to the peak power of 0.247, 30.1, 37.6, and 10.1 W. The pulse energy of AOM/SnSe₂ doubly Q-switched laser ($f_A = 5$ kHz) was 74 times higher than that of SnSe₂ singly Q-switched laser. Because of the pulse compression and pulse energy improvement in doubly Q-switched laser, compared with the singly Q-switched laser with SnSe₂, the pulse peak power of doubly Q-switched laser with AOM/SnSe₂ ($f_A = 5$ kHz) was basically raised 152 times.

Considering the degradation of optical parameters of SnSe₂-SA, in order to check the robustness of SnSe₂-SA, the doubly Q-switched laser with AOM and SnSe₂-SA was kept operating at the maximum radiation power for at least 6 h every day during 1 week. The fluctuation of the average output power ΔP is measured less than 4.1% at the pump power of 8 W. Besides, no damage and optical degradation of the SnSe₂-SA was observed in the experiment.



AOM/SnSe₂ Q-switched laser), at 8 W maximum pump power and $f_A = 5$ kHz. The typically extended temporal profiles of Q-switching pulses at the pump power of 8 W was illustrated in **Figure 6**. As a solid state laser with free space configuration, the beam quality was measured by the 90.0/10.0 scanning-knife-edge method, the beam quality factors (M^2) in the horizontal and longitudinal planes are 1.68/1.38.

The pulse repetition rate versus the pump power for SnSe₂ singly Q-switched laser was given in **Figure 7**. The pulse repetition rates varied from 79.6 to 479 kHz within the pump range of 1.5–8 W. The dependences of pulse energies and peak powers on the pump power are depicted in **Figure 8**. Both pulse energies and peak powers increase monotonically with the increasing of the pump power. Under the maximum pump power of

4 CONCLUSION

In conclusion, based on the AOM and SnSe₂ film, a diode-pumped doubly Q-switched laser with high peak power and adjustable repetition rate was presented. The experimental results show the relations of the pulse width, pulse energy and pulse peak power of the Q-switched pulses versus the repetition rate of AOM and the pump power. In our experiment, the maximum pulse peak power of 37.57 KW with minimum pulse duration of 5.52 ns was obtained with the maximum pump power of 8 W and AOM repetition rate of 5 kHz. A lower repetition rate is conducive to obtaining pulses with high peak power. Compared with the singly passively Q-switched lasers with SnSe₂-SA, the pulse characteristics of this doubly Q-switched laser were improved significantly. The experimental results demonstrate that the dual-loss modulation technology is an

effective method to compress the pulse width and obtain the pulses with controllable repetition rate and high peak power.

DATA AVAILABILITY STATEMENT

The original contributions presented in the study are included in the article/supplementary material, further inquiries can be directed to the corresponding author.

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AUTHOR CONTRIBUTIONS

JX conceived and designed the experiments, performed the experiments and analysed the data, drafted the manuscript; XD fabricated and characterized the SnSe₂ saturable absorber; HY contributed to perform the theoretical analysis, all authors contributed to writing and editing the manuscript. All authors have read and agreed to the published version of the manuscript.

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